

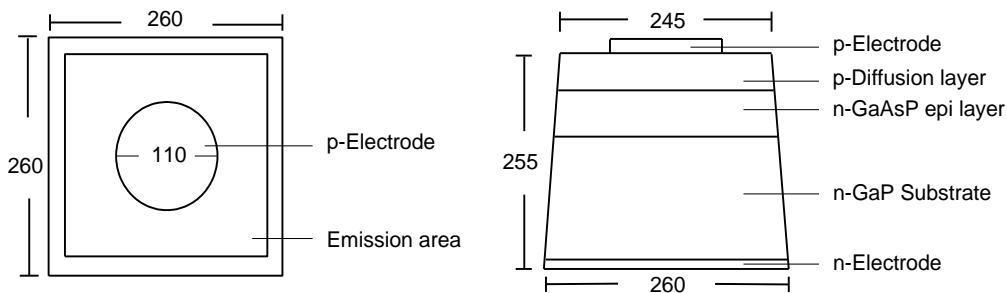
Features :

- GaAsP/ GaP Epi Wafer

Typical Applications :

- Lamp
- SMD
- Display
- Dot Matrix

Outline Dimensions : (Unit:um)



Physical Structure :

Chip dimension	Chip size	260 um x 260 um
	Thickness	255 um
	Emission area	245 um
	Bonding pad	110 um
Electrode	Top: P (anode)	Aluminum (Gold optional)
	Backside: N (cathode)	Gold alloy
Surface condition	Not frosted	

Electro-Optical Characteristics : (Ta = 25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20 \text{ mA}$	-	-	2.60	V
Reverse Current	I_R	$V_R = 5 \text{ V}$	-	-	10	μA
Wavelength	λ_P	$I_F = 20 \text{ mA}$	-	632	-	nm
	Hue		615	620	629	
Spectral width at half height	$\Delta \lambda$	$I_F = 20 \text{ mA}$	-	35	-	nm
Luminous Intensity	I_v	$I_F = 20 \text{ mA}$	7.0	-	-	mcd